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FORM PTO-1449 (MODIFIED)  APR 11 2005 22  LIST OF PATENTS AND  PUBLICATIONS				ATTORNEY DOCKET NO. SP03-077			SERIAL NO. 10/622606			
FOR APPLICANTS INFORMATION DISCLOSURE STATEMENT				APPLICANT: James G. Couillard, et al.						
			·	FILING DATE July 1		GI	ROUP:	2811		
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